

## ABSTRACT

A method of fabricating a resistor in which the resistance value of the resistor is measured and adjusted after silicidation is provided. The method of the present invention begins with first providing at least one resistor, e.g., polysilicon, having a resistance value on a surface of a semiconductor substrate. The at least one resistor has been subjected to a silicidation process. Next, the resistance value of the at least one resistor is measured to determine the actual resistance of the resistor after silicidation. After the measuring step, the resistance of the resistor is adjusted to achieve a desired resistance value. The adjusting may include a post silicidation rapid thermal anneal and/or a post silicidation ion implantation and a low temperature rapid thermal anneal step.